

Dual P-Ch 30V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

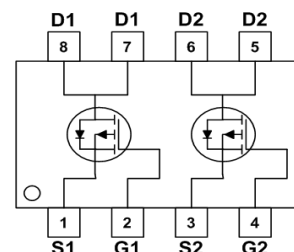
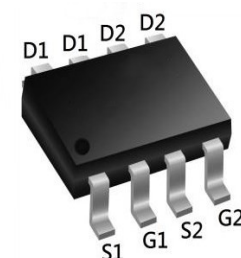


BVDSS	RDSON	ID
-30V	12mΩ	-11A

Description

The XR4805A is the highest performance trenched P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XR4805A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _C = 25°C	-11	A
		T _C = 100°C	-8	A
I _{DM}	Pulsed Drain Current ^{note1}		-40	A
P _D	Power Dissipation	T _A = 25°C	3.7	W
R _{θJA}	Thermal Resistance, Junction to Ambient		33.8	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C

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Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} =0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance Note3	V _{GS} = -10V, I _D = -10A	-	12	15	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	18	27	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} =0V, f=1.0MHz	-	1330	-	pF
C _{oss}	Output Capacitance		-	183	-	pF
C _{rss}	Reverse Transfer Capacitance		-	156	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -5A, V _{GS} = -10V	-	22	-	nC
Q _{gs}	Gate-Source Charge		-	1.0	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	1.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -10A, V _{GS} =-10V, R _{GEN} =2.5Ω	-	9	-	ns
t _r	Turn-on Rise Time		-	13	-	ns
t _{d(off)}	Turn-off Delay Time		-	48	-	ns
t _f	Turn-off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-11	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -15A	-	-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	T _J =25℃,	-	64	-	ns
Q _{rr}	Reverse Recovery Charge	V _{DD} = -24V, I _F =-2.8A, dI/dt=-100A/μs	-	25	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_{GS}=10V, R_G=25Ω, L=0.5mH, I_{AS}=-12.7A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

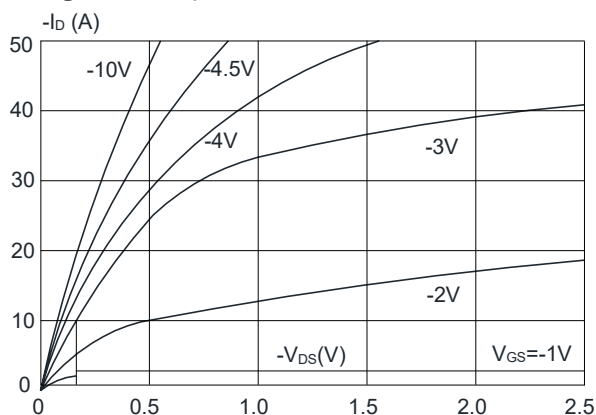


Figure 2: Typical Transfer Characteristics

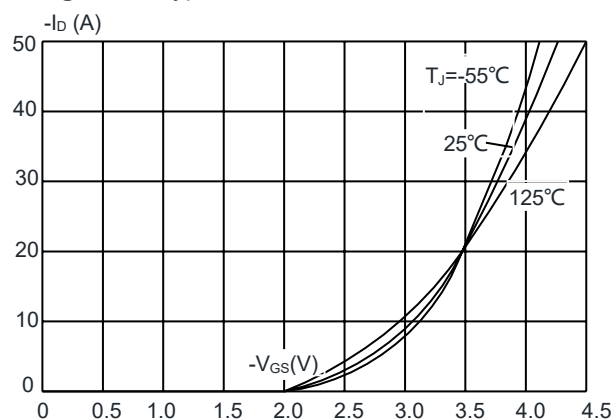


Figure 3: On-resistance vs. Drain Current

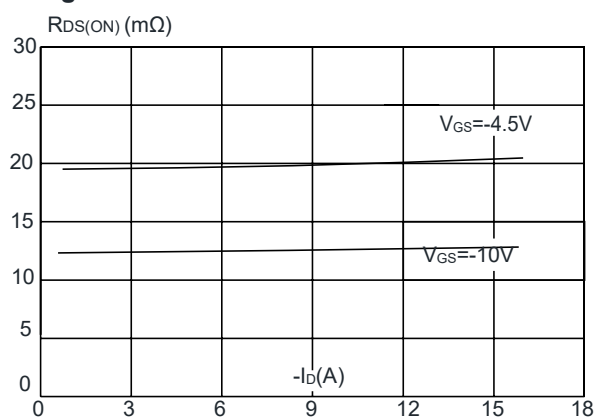


Figure 4: Body Diode Characteristics

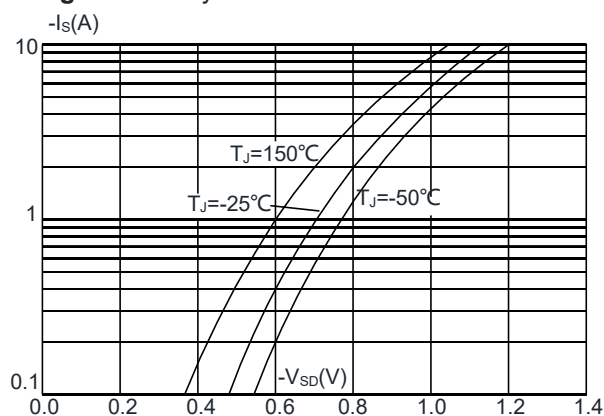


Figure 5: Gate Charge Characteristics

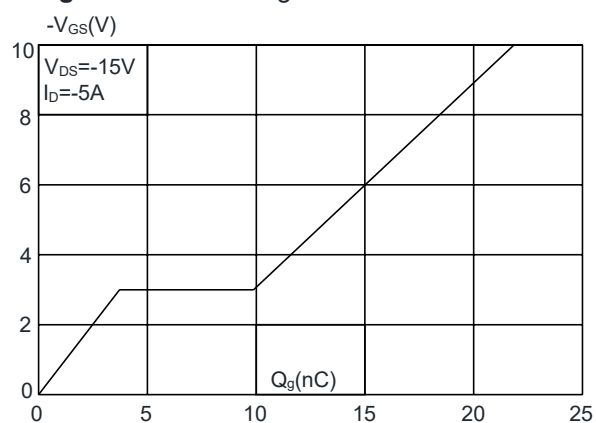
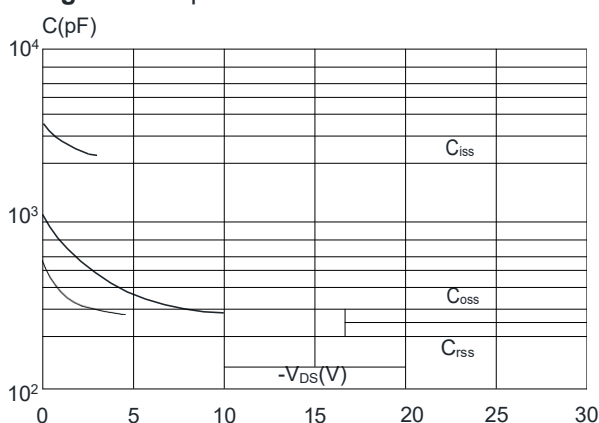


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

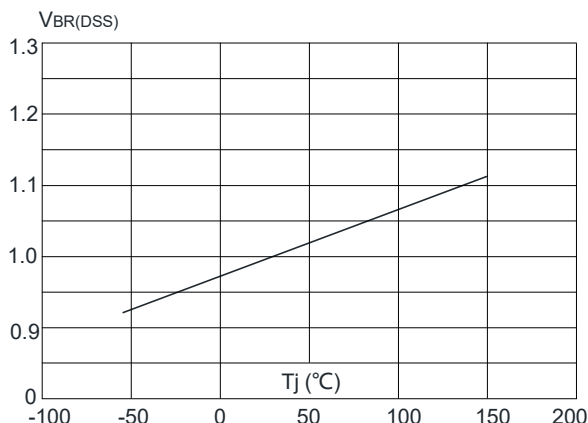


Figure 8: Normalized on Resistance vs. Junction Temperature

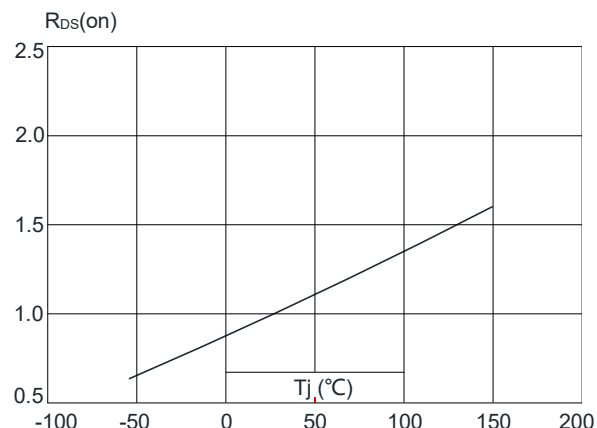


Figure 9: Maximum Safe Operating Area

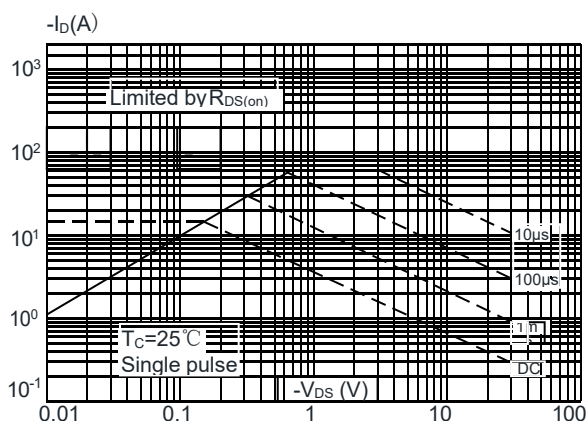


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

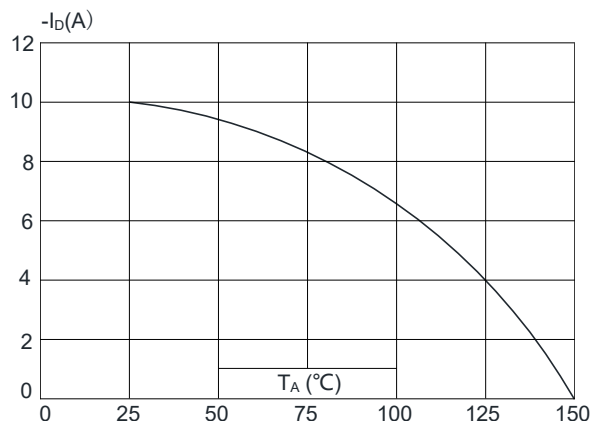
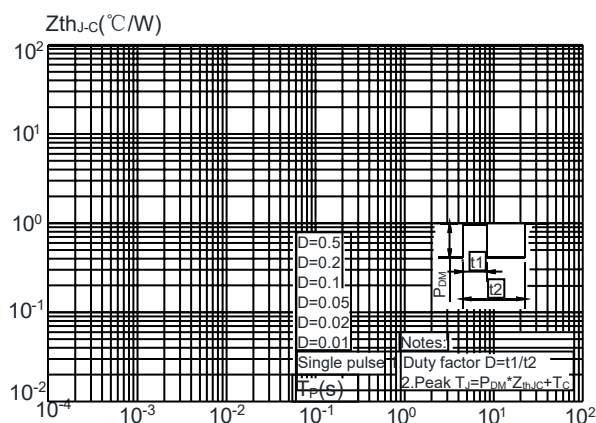
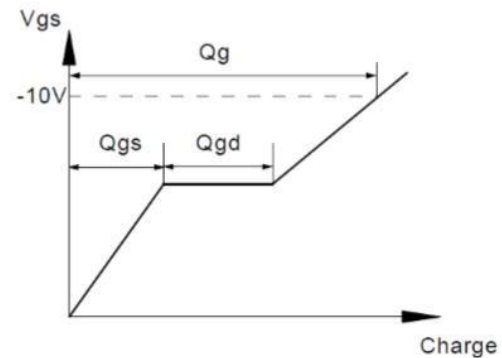
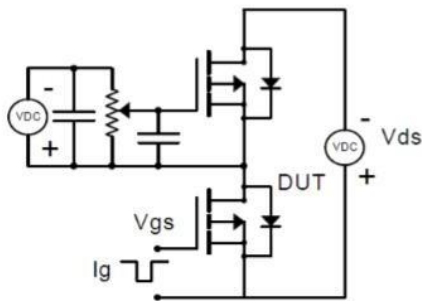


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

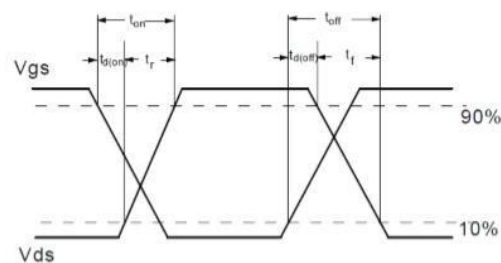
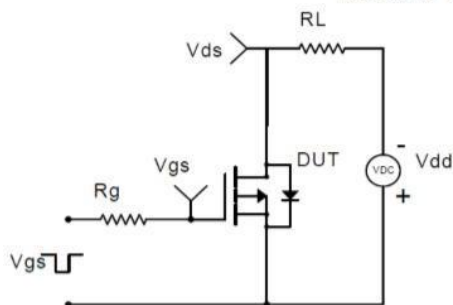


Test Circuit

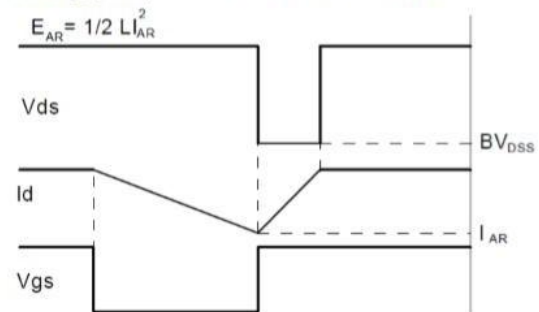
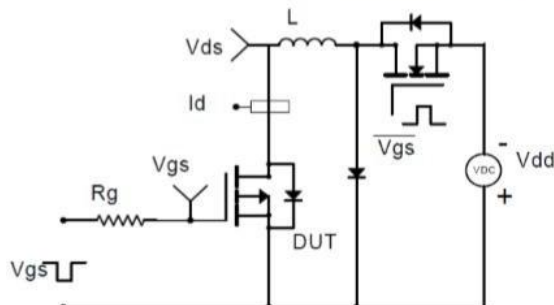
Gate Charge Test Circuit & Waveform



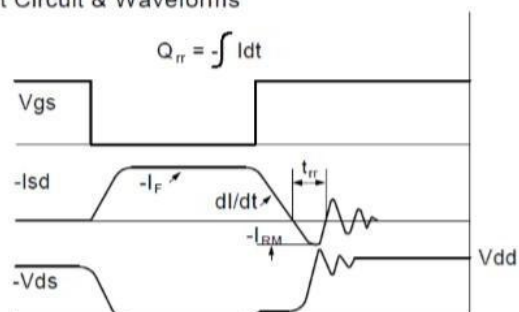
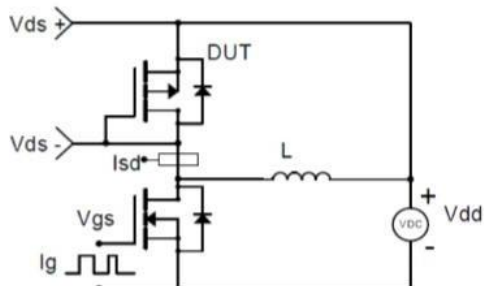
Resistive Switching Test Circuit & Waveforms



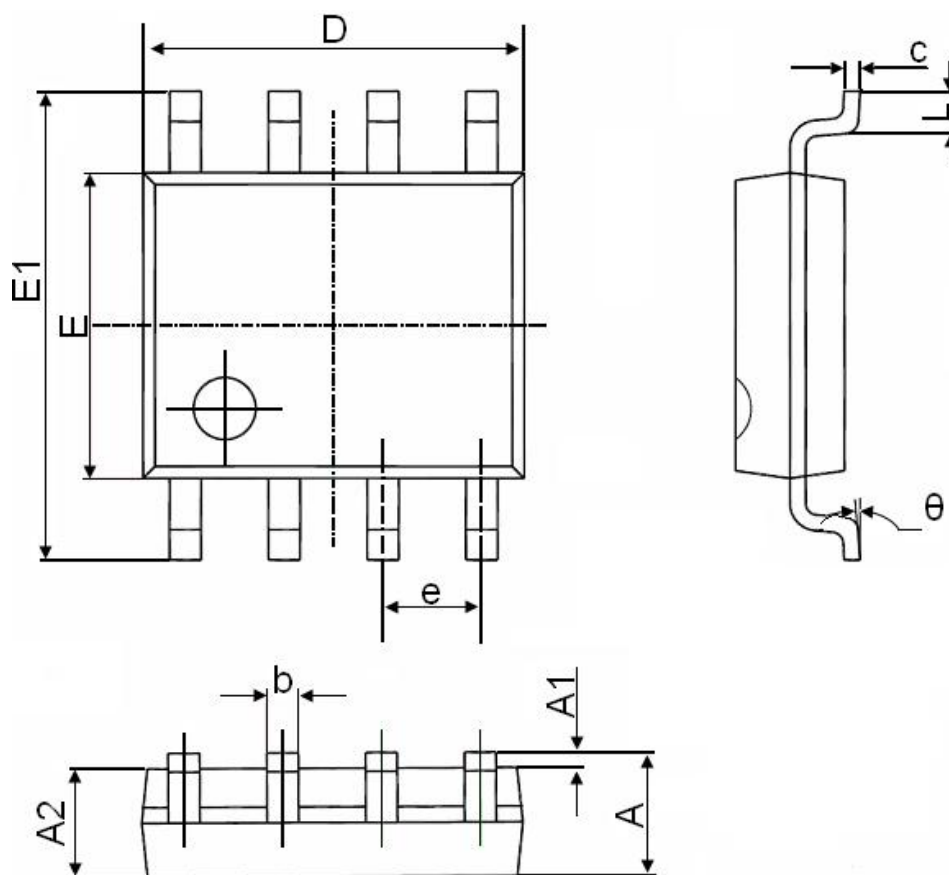
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°